2187

Atty Docket No.: RBS2.P031

PATENT

IN THE UNITED STATES PATENT OFFICE

In Re Patent Application of:

First Named Inventor: Garrett, Jr., Billy

Application No.: 09/837,307

Filed: 4/17/2001

Title: MECHANISM FOR ENABLING FULL DATA BUS UTILIZATION WITHOUT INCREASING DATA GRANULARITY

Examiner: Dinh, Ngoc V.

Art Unit: 2187

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria VA 22313-1450 on July 25, 2005

Kyle S. Okada

(Name of Person Mailing Correspondence)

Signature Date July 25, 2005

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

Sir:

Enclosed is an Information Disclosure Citation Form 1449/PTO together with a copy of each reference cited therein, excluding U.S. Patents and Published U.S. Patent Applications. It is respectfully requested that the cited references be considered and that the enclosed copy of the Form 1449/PTO be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant.

This Information Disclosure Statement is being submitted pursuant to 37 CFR 1.97(b). No fee is believed to be due.

Pursuant to 37 CFR 1.97(h), the submission of this Information Disclosure Statement is not to be construed as an admission that the information cited in this statement is material to patentability.

The Commissioner is hereby authorized to charge any fees which may be required in connection with this submission to Deposit Account No. 501914.

Respectfully submitted,

SHEMWELL GREGORY & COURTNEY LLP

Date July 25, 2005

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Examiner Initials*	US Patent Document Number	Kind	Name of Patentee or Applicant of Cited Document	Date of Publication	Relevant Pages, Columns, Lines
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